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**MAY 2022 (INSEM+ ENDSEM) EXAM**  
**F.Y. B. TECH. (SEMESTER - II)**  
**COURSE NAME: BASIC ELECTRONICS ENGINEERING**  
**COURSE CODE: ET10203B**  
**(PATTERN 2020)**

Time: [2Hr]

[Max. Marks: 60]

**(\*) Instructions to candidates:**

- 1) Figures to the right indicate full marks.
- 2) Use of scientific calculator is allowed
- 3) Use suitable data where ever required

**Q.1****Solve the following**

- i) In Half Wave Rectifier, if peak value of output is 17.5 V, then the peak value of its input is \_\_\_\_\_ [2]
  - a) 17.5 V
  - b) 22.5 V
  - c) 16.8 V
  - d) 18.2 V
- ii) A half-wave rectifier has an input voltage of 240 V r.m.s. If the step-down transformer has a turns ratio of 8:1, what is the peak load voltage? (consider Si diode drop) [2]
  - a) 27.5 V
  - b) 86.5 V
  - c) 41.7 V
  - d) 42.4 V
- iii) A forward potential of 15V is applied to a Si diode. A resistance of 5 K $\Omega$  is also in series with the diode (Assume practical diode model). The current is---- [2]

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  - a) 2.86 mA
  - b) 1.5 mA
  - c) 3 mA
  - d) 0.7 mA
- iv) A half-wave rectifier with Si diode has input voltage of 170 V peak. If the step-down transformer has turns ratio of 2:1, what is the peak output voltage? [2]
  - a) 48.3 V
  - b) 40.7 V
  - c) 84.3 V
  - d) 1.4 V

- v) What is the minimum PIV rating of each diode in center tap full wave rectifier, if its  $V_p(\text{out})$  is equal to 24.3 V? [2]  
 a) 49.3 V  
 b) 24.7 V  
 c) 48.6 V  
 d) 1.4 V
- vi) Determine the peak output voltage for the full wave bridge rectifier. Assume silicon diode. The transformer is specified to have a 10 V rms secondary voltage and 120 V across the primary winding. [2]  
 a) 8.6 V  
 b) 12.74 V  
 c) 14.14 V  
 d) 93.7 V
- vii) Determine the PIV rating for the full wave bridge rectifier. Assume all four are silicon diodes. The transformer is specified to have a 12 V rms as secondary voltage for the standard 140 V across the primary. [2]  
 a) 16.3 V  
 b) 10 V  
 c) 8.2 V  
 d) 15 V
- viii) The average value of Half-Wave rectified output voltage is \_\_\_\_\_ if its peak output voltage is 20 V. [2]  
 a) 20.28 V  
 b) 6.37V  
 c) 9.54 V  
 d) 20.7 V
- ix) In a transistor,  $I_C = 100 \text{ mA}$  and  $I_E = 100.2 \text{ mA}$ . The value of  $\beta$  is ..... [2]  
 a) 50  
 b) 500  
 c) 100  
 d) 200
- x) In a transistor if  $\beta = 100$  and collector current  $I_C$  is 10 mA, then the emitter current  $I_E$  is ..... [2]  
 a) 100.1 mA  
 b) 110 mA  
 c) 10.1 mA  
 d) 15 mA
- xi) The current gain ( $\beta$ ) of a transistor in common emitter configuration is 40. If the collector current changes by 160mA, then required change in the base current is .....for constant VCE. [2]  
 a) 4 mA  
 b) 0.4 mA  
 c) 40 mA  
 d) 4 A

- xii) In RC phase shift oscillator producing output at  $f = 500 \text{ Hz}$ ,  $R = 7.5 \text{ Kohm}$  then  $C = \text{---}$ .  
 a) 0.01 micro F  
 b) 0.017 micro F  
 c) 0.012 nanoF  
 d) 0.001 micro F
- xiii) Determine value of collector current  $I_c$ , for  $\beta=150$  and  $I_B= 430 \mu\text{A}$ . [2]  
 a) 100 mA  
 b) 46.8 mA  
 c) 64.5 mA  
 d) 80.3 mA
- xiv) For voltage divider biasing circuit, if  $R_1=100 \text{ K}\Omega$ ,  $R_2= 15 \text{ K}\Omega$ ,  $V_{CC}=24\text{V}$ . [2]  
 What is the value of  $V_B$  (voltage at Base terminal) ?  
 a) 3.13 V  
 b) 4.53 V  
 c) 24 V  
 d) 12 V
- xv) For a BJT fixed bias circuit, determine base current  $I_B$ , if  $V_{BB}=5\text{V}$   $V_{BE} = 0.7\text{V}$  [2]  
 and  $R_B = 10\text{K}\Omega$ .  
 a) 650  $\mu\text{A}$   
 b) 430  $\mu\text{A}$   
 c) 340  $\mu\text{A}$   
 d) 100  $\mu\text{A}$

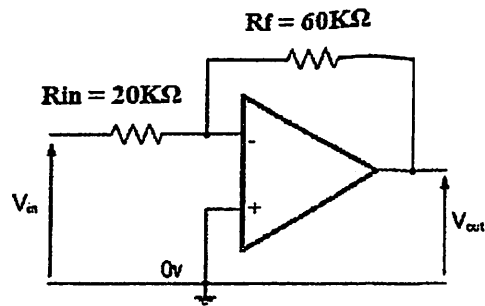
**Q.2 Solve any three questions out of four**

- a) Sketch the internal structure of n-channel Enhancement type MOSFET and explain its transfer characteristics? [5]
- b) Calculate  $V_{GS}$  and  $V_{DS}$  for E-MOSFET voltage divider biasing circuit, with  $R_1=200 \text{ K}\Omega$ ,  $R_2=20 \text{ K}\Omega$ ,  $R_D= 200 \Omega$ ,  $R_S=0 \Omega$  and  $V_{DD} = 20 \text{ V}$ . Assume this particular E-MOSFET has minimum values of  $I_{D(on)}= 200 \text{ mA}$  at  $V_{GS} = 4 \text{ V}$  and  $V_{GS(th)} = 1 \text{ V}$ . [5]
- c) Draw and explain V-I characteristics of SCR for different values of gate current. [5]
- d) Draw and explain Turn OFF process of SCR with circuit diagram [5]

**Q.3 Solve any three questions out of four**

- a) Draw op-amp IC 741 symbol and explain the importance of its each terminal. [5]
- b) Explain the following terms related to a op-amp with necessary diagrams [5]  
 i) Virtual ground  
 ii) Slew Rate

- c) Calculate closed loop gain of the circuit shown below and also find out its output voltage if 1.5 V of DC input signal is applied to the circuit. [5]



- d) With the help of block diagram explain different blocks of OPAMP. [5]

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